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(INVITED)

Recent Developments in Microwave Devices

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Progress in solid state devices is achieved through a number of factors which include improving the understanding of the device physics, the device material, the device technology and packaging, and the understanding of the device/circuit interaction. This paper reviews the recent advances in the microwave properties of a number of different solid state devices and relates them to these factors. This includes the recent spectacular worldwide progress in gallium arsenide field-effect transistors as well as the significant progress in indium phosphide transferred-electron devices and gallium arsenide and silicon avalanche devices. -----

